

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. <u>Unknown</u> 9/258643
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: <u>Unknown</u> 2822

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<u>MT</u>	4,460,670	07/01/1984	Ogawa, et al.	430	57	11/19/82
	4,507,673	03/26/1985	Aoyama, M., et al.	357	23 R	09/21/83
	4,657,699	04/01/1987	Nair	252	513	12/17/84
	4,738,729	04/01/1998	Yoshida, et al.	136	258	01/27/87
	4,769,686	09/06/1988	Horiuchi, M., et al.	357	23.8	06/19/87
	4,893,273	01/09/1990	Usami	365	185	03/21/86
	5,111,430	05/05/1992	Morie	365	185	06/21/90
	5,145,741	09/01/1992	Quick	428	402	02/28/91
	5,260,593	11/09/1993	Lee, R.R.	257	316	12/10/91
	5,293,560	03/08/1994	Harari	365	185	11/03/92
	5,298,796	03/29/1994	Tawel, R.	307	201	07/08/92
	5,369,040	11/29/1994	Halvis, et al.	437	3	04/12/93
	5,449,941	09/12/1995	Yamazaki, S., et al.	257	411	10/27/92
	5,465,249	11/07/1995	Cooper, et al.	365	149	11/26/91
	5,477,485	12/19/1995	Bergemont, et al.	365	185.24	02/22/95
	5,508,543	04/16/1996	Hartstein, et al.	257	314	04/29/94
	5,530,581	06/25/1996	Cogan	359	265	05/31/95
	5,580,380	12/03/1996	Liu, et al.	117	86	01/30/95
	5,604,357	02/18/1997	Hori, T.	257	24	07/11/95
	5,623,442	04/22/1997	Gotou, H., et al.	365	185.08	06/08/94
	5,629,222	05/13/1997	Yamazaki, S., et al.	438	259	04/28/95
	5,670,790	09/23/1997	Katoh, et al.	257	14	09/19/96
	5,714,766	02/03/1998	Chen, et al.	257	20	09/29/95
	5,740,104	04/14/1998	Forbes, L.	365	185.03	01/29/97
	5,754,477	05/19/1998	Forbes, L.	365	185.33	01/29/97
	5,786,250	07/28/1998	Wu, Z., et al.	438	254	03/14/97
	5,801,401	09/01/1998	Forbes, L.	257	77	01/29/97

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
<u>MT</u>	3-222367	10/01/1991	Japan	H01L	29/784	<input checked="" type="checkbox"/> <input type="checkbox"/>
<u>MT</u>	6-224431	08/12/1994	Japan	H01L	29/784	<input checked="" type="checkbox"/> <input type="checkbox"/>
<u>MT</u>	6-302828	10/28/1994	Japan	H01L	29/788	<input checked="" type="checkbox"/> <input type="checkbox"/>
<u>MT</u>	8-255878	10/01/1996	Japan	H01L	27/10	<input checked="" type="checkbox"/> <input type="checkbox"/>

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial

Examiner <u>Michael T. R. L.</u>	Date Considered <u>6/30/00</u>
----------------------------------	--------------------------------

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

91256643

Sheet 2 of 9

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown 282

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
Initial

MT	Akasaki, I., et al., "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga(1-x)Al(x)N [0 < x (< or =) 0.4] Films Grown on Sapphire Substrate by MOVPE", <u>J. Crystal Growth</u> , 98, 209-219, (1989)
MT	Alok, D., et al., "Electrical Properties of Thermal Oxide Grown on N-type 6H-Silicon Carbide", <u>Applied Physics Letters</u> , 64, 2845-2846, (May 23, 1994)
MT	Andrieux, M., et al., "Interface and Adhesion of PACVD SiC Based Films on Metals", <u>Supp. "Le Vide: science, technique et applications"</u> , 279, 212-214, (1996)
MT	Bachmann, P., et al., "Influence on Surface Modifications on the Electronic Properties of CVD Diamond Films", <u>Diamond and Related Materials</u> , 5, 1378-1383, (1996)
MT	Baglee, D., "Characteristics & Reliability of 100 Angstrom Oxides", <u>IEEE 22nd Annual Proc.: Reliability Physics</u> , Las Vegas, 152-155, (April 3-5, 1984)
	Beheim, G., et al., "Magnetron Plasma Etching of SiC for Microstructures", <u>Proc: SPIE - Integrated Optics and Microstructures III</u> , San Jose, CA, 82-86, (Jan 29, 1996)
	Bengtsson, S., et al., "Applications of Aluminum Nitride Films Deposited by Reactive Sputtering to Silicon-On-Insulator Materials", <u>Japanese J. Applied Physics</u> , 35, 4175-4181, (1996)
	Benjamin, M., et al., "UV Photoemission Study of Heteroepitaxial AlGaIn Films Grown on 6H-SiC", <u>Applied Surface Science</u> , 104/105, 455-460, (1996)
	Bermudez, V., et al., "The Growth and Properties of Al and AlN Films on GaN(0001)-(1 x 1)", <u>J. Applied Physics</u> , 79, 110-119, (Jan. 1996)
	Casey, H., et al., "Low Interface Trap Density for Remote Plasma Deposited SiO2 on n-type GaN", <u>Applied Phys. Lett.</u> , 68, 1850-1852, (March 1996)
MT	Chang, C., et al., "Novel Passivation Dielectrics-The Boron- or Phosphorus-Doped Hydrogenated Amorphous Silicon Carbide Films", <u>Journal of the Electrochemical Society</u> , 132, 418-422, (Feb. 1985)

Examiner

Michael Trinh

Date Considered

6/20/00

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
Initial

mt	Choi, J., et al., "Effect of Deposition Conditions and Pretreatments on the Microstructure of MPECVD Diamond Thin Films", <u>Materials Chemistry and Physics</u> , <u>45</u> , 176-179, (1996)
	Clarke, G., et al., "The Infrared Properties of Magnetron-Sputtered Diamond-Like Thin Films", <u>Thin Solid Films</u> , <u>280</u> , 130-135, (1996)
	Compagnini, G., et al., "Spectroscopic Characterization of Annealed Si(1-x)C(x) Films", <u>J. Materials Res.</u> , <u>11</u> , 2269-2273, (Sept. 1996)
	Dartnell, N., et al., "Reactive Ion Etching of Silicon Carbide (Si(x)C(1-x))", <u>Vacuum</u> , <u>46</u> , 349-355, (1995)
	Demichelis, F., et al., "Influence of Doping on the Structural and Optoelectronic Properties of Amorphous and Microcrystalline Silicon Carbide", <u>Journal of Applied Physics</u> , <u>72</u> , 1327-1333, (Aug. 15, 1992)
	Demichelis, F., et al., "Physical Properties of Undoped and Doped Microcrystalline SiC:H Deposited By PECVD", <u>Materials Research Society Symposium Proceedings</u> , <u>219</u> , Anaheim, CA, 413-418, (4/30 - 5/3, 1991)
	Dipert, B., et al., "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , <u>30</u> , 48-52, (1993)
	Fissel, A., et al., "Epitaxial Growth of SiC Thin Films on Si-stabilized alpha-SiC (0001) at Low Temperatures by Solid-source Molecular Beam Epitaxy", <u>Journal of Crystal Growth</u> , <u>154</u> , 72-80, (1995)
	Friedrichs, P., et al., "Interface Properties of Metal-Oxide-Semiconductor Structures on N-Type 6H and 4H-SiC", <u>J. Applied Physics</u> , <u>79</u> , 7814-7819, (May 15, 1996)
	Fujii, T., et al., "Bonding Structures in Highly Photoconductive a-SiC:H Films Deposited by Hybrid-Plasma Chemical Vapor Deposition", <u>Journal of Non-Crystalline Solids</u> , <u>198-200</u> , 577-581, (1996)
	Goetzberger, A., et al., <u>Applied Solid State Science: Advances in Materials and Device Research</u> , R. Wolfe, ed., Academic Press, New York, Including pg. 233, (1969)
mt	Graul, J., et al., "Growth Mechanism of Polycrystalline beta-SiC Layers on Silicon Substrate", <u>Applied Phys. Lett.</u> , <u>21</u> , 67-69, (July 1972)

Examiner

Michael Trach

Date Considered

6/30/00

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
Initial

MS	Hamakawa, Y., et al., "Optoelectronics and Photovoltaic Applications of Microcrystalline SiC", <u>Materials Research Society Symposium Proceedings</u> , 164, Boston, MA, 291-301, (11/29-12/1, 1989)
	He, Z., et al., "Ion-beam-assisted Deposition of Si-carbide Films", <u>Thin Solid Films</u> , 260, 32-37, (1995)
	Hu, G., et al., "Will Flash Memory Replace Hard Disk Drive?", <u>1994 IEEE International Electron Device Meeting</u> , Panel Discussion, Session 24, Outline, 1 p., (Dec. 13, 1994)
	Hwang, J., et al., "High Mobility beta-SiC Epilayer Prepared by Low-pressure Rapid Thermal Chemical Vapor Deposition on a (100) Silicon Substrate", <u>Thin Solid Films</u> , 272, 4-6, (1996)
	Jou, S., et al., "Electron Emission Characterization of Diamond Thin Films Grown from a Solid Carbon Source", <u>Thin Solid Films</u> , 280, 256-261, (1996)
	Kothandaraman, M., et al., "Reactive Ion Etching of Trenches in 6H-SiC", <u>J. Electronic Materials</u> , 25, 875-878, (1996)
	Kumbhar, A., et al., "Growth of Clean Amorphous Silicon-Carbon Alloy Films by Hot-Filament Assisted Chemical Vapor Deposition Technique", <u>Applied Phys. Lett.</u> , 66, 1741-1743, (April 1995)
	Lakshmi, E., et al., "Interface-State Characteristics of GaN/GaAs MIS Capacitors", <u>Solid-State Electronics</u> , 25, 811-815, (1982)
	Lanois, F., et al., "Angle Etch Control for Silicon Carbide Power Devices", <u>Applied Phys. Lett.</u> , 69, 236-238, (July 1996)
	Lau, S., et al., "Optoelectronic Properties of Highly Conductive Microcrystalline SiC Produced by Laser Crystallization of Amorphous SiC", <u>J. of Non-Crystalline Solids</u> , 198-200, 907-910, (1996)
	Leggieri, G., et al., "Laser Ablation Deposition of Silicon Carbide Films", <u>Applied Surface Science</u> , 96-98, 866-869, (1996)
NT	Lei, T., et al., "Epitaxial Growth and Characterization of Zinc-Blende Gallium Nitride on (001) Silicon", <u>J. Appl. Phys.</u> , 71, 4933-4943, (May 1992)

Examiner	Michael Trill	Date Considered	6/30/96
----------	---------------	-----------------	---------

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
Initial

m	Liu, J., et al., "Formation of SiC Films on Silicon Field Emitters", <u>Materials Res. Soc. Symp. Proc.</u> , 311, San Francisco, CA, (April 13-15, 1993)
	Liu, J., et al., "Modification of Si Field Emitter Surfaces by Chemical Conversion to SiC", <u>J. Vac. Sci. Technology</u> , B 12, 717-721, (1994)
	Luo, J., et al., "Localized Epitaxial Growth of Hexagonal and Cubic SiC Films on Si by Vacuum Annealing", <u>Applied Phys. Lett.</u> , 69, 916-918, (Aug. 1996)
	Martins, R., et al., "Transport Properties of Doped Silicon Oxycarbide Microcrystalline Films Produced by Spatial Separation Techniques", <u>Solar Energy Materials and Solar Cells</u> , 41-42, 493-517, (1996)
	Martins, R., et al., "Wide Band Gap Microcrystalline Silicon Thin Films", <u>Diffusion and Defect Data : Solid State Phenomena</u> , 44-46, Part 1, Scitec Publications, 299-346, (1995)
	Maury, F., et al., "Chemical Vapor Co-Deposition of C and SiC at Moderate Temperature for the Synthesis of Compositionally Modulated Si(x)C(1-x) Ceramic Layers", <u>Surface and Coatings Technology</u> , 76-77, 119-125, (1995)
	McLane, G., et al., "High Etch Rates of SiC in Magnetron Enhanced SF(6) Plasmas", <u>Applied Phys. Lett.</u> , 68, 3755-3757, (June 1996)
	Mogab, C., et al., "Conversion of Si to Epitaxial SiC by Reaction with C(2)H(2)", <u>J. Applied Physics</u> , 45, 1075-1084, (March 1974)
	Molnar, R., et al., "Growth of Gallium Nitride by Electron-Cyclotron Resonance Plasma-Assisted Molecular-Beam Epitaxy: The Role of Charged Species", <u>J. Appl. Phys.</u> , 76, 4587-4595, (1994)
	Muller, K., et al., "Trench Storage Node Technology for Gigabit DRAM Generations", <u>Digest IEEE International Electron Devices Meeting</u> , San Francisco, CA, 507-510, (Dec. 1996)
m	Nemanich, P., et al., "Diamond Negative Electron Affinity Surfaces, Structures and Devices", <u>Proc. : Third International Conference on Applications of Diamond Films and Related Materials</u> , 1, Gaithersburg, MD, 17-24, (1995)
	Nemanich, R., et al., "Negative Electron Affinity Surfaces of Aluminum Nitride and Diamond", <u>Diamond and Related Materials</u> , 5, 790-796, (1996)

Examiner

Michael Trinch

Date Considered

6/80

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

9/256,643

Sheet 6 of 9

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown 282~

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
Initial

<i>ms</i>	Ouyang, M., et al., "Deposition of Diamond-Like Carbon Films via Excimer Laser Ablation of Polybutadiene", <u>Materials Science and Engineering</u> , B39, 228-231, (1996)
	Pankove, J., "Photoelectric Emission", <u>In: Optical Processes in Semiconductors</u> , Dover Publications Inc., New York, 287-301, (1971)
	Pankove, J., et al., "Photoemission from GaN", <u>Applied Phys. Lett.</u> , 25, 53-55, (1974)
	Papadas, C., et al., "Modeling of the Intrinsic Retention Characteristics of FLOTOX EEPROM Cells Under Elevated Temperature Conditions", <u>IEEE Transaction on Electron Devices</u> , 42, 678-682, (April 1995)
	Patuwathavithane, C., et al., "Oxidation Studies for 6H-SiC", <u>Proc. 4th Int. Conf. on Amorphous and Crystalline Silicon Carbide IV</u> , Santa Clara, CA, 163-169, (Oct. 9-11, 1991)
	Pereyra, I., et al., "Wide Gap a-Si(1-x)C(x): H Thin Films Obtained Under Starving Plasma Deposition Conditions", <u>J. Non-Crystalline Solids</u> , 201, 110-118, (1996)
	Pollack, S., "Electron Transport Through Insulating Thin Films", <u>Appl. Solid-State Science</u> , 1, 345-355, (1969)
	Prendergast, J., "FLASH or DRAM: Memory Choice for the Future", <u>IEEE Electron Device Meeting, Session 25</u> , Phoenix, AZ, (1995)
	Rahman, M., et al., "Preparation and Electrical Properties of An Amorphous. SiC/ Crystalline Si p(+)n Heterostructure", <u>Japanese J. Applied Physics</u> , 23, 515-524, (May 1984)
	Renlund, G., et al., "Silicon Oxycarbide Glasses: Part I. Preparation and Chemistry", <u>Journal of Materials Research</u> , 6, 2716-2722, (December 1991)
	Renlund, G., et al., "Silicon Oxycarbide Glasses: Part II. Structure and Properties", <u>Journal of Materials Research</u> , 6, 2723-2734, (December 1991)
<i>ms</i>	Schmidt, I., et al., "Low Temperature Diamond Growth Using Fluorinated Hydrocarbons", <u>Diamond and Related Materials</u> , 5, 1318-1322, (1996)

Examiner

Michael Trail

Date Considered

6/30/00

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
Initial

mt	Serre, C., et al., "Ion-Beam Synthesis of Amorphous SiC Films: Structural Analysis and Recrystallization", <u>J. Appl. Phys.</u> , <u>79</u> , 6907-6913, (May 1996)
	Sim, S., et al., "A New Planar Stacked Technology (PST) for Scaled and Embedded DRAMs", <u>Digest IEEE Int. Electron Devices Meeting</u> , San Francisco, CA, 504-507, (Dec. 1996)
	Suzaki, Y., et al., "Quantum Size Effects of a-Si(:H)/a-SiC(:H) Multilayer Films Prepared by rf Sputtering", <u>Abstracts of Papers Published in the Int. J. Japanese Soc. for Precision Engineering</u> , <u>28</u> , Abstract of Paper in vol. 60, 182, (June 1994)
	Svirkova, N., et al., "Deposition Conditions and Density-of-States Spectrum of a-Si(1-x)C(x) :H Films Obtained by Sputtering", <u>Semiconductors</u> , <u>28</u> , 1164-1169, (Dec. 1994)
	Sze, S., <u>Physics of Semiconductors</u> , 2nd Edition., John Wiley & Sons, Pub., New York, ISBN 0471056618, (1981)
	Tarui, Y., "Flash Memory Features Simple Structure, Superior Integration", <u>JEE</u> , <u>30</u> , 84-87, (Sept. 1993)
	Tenhover, M., et al., "DC-Magnetron Sputtered Silicon Carbide", <u>Materials Res. Soc. Symp. Proc.</u> , <u>356</u> , Boston, MA, 227-232, (11/28-12/02, 1994)
	Thomas, J., et al., "Plasma Etching and Surface Analysis of a-SiC :H Films Deposited by Low Temperature Plasma Enhanced Chemical Vapor Deposition", <u>Materials Res. Soc. Symp. Proc.</u> , <u>334</u> , Boston, MA, 445-450, (11/29-12/02, 1993)
	Tiwari, S., et al., "A silicon nanocrystal based memory", <u>Appl. Physics Lett.</u> , <u>68</u> , 1377-1379, (1996)
	Tiwari, S., et al., "Volatile and Non-Volatile Memories in Silicon with Nano-Crystal Storage", <u>Int'l Electron Devices Meeting: Technical Digest</u> , Washington, DC, 521-524, (Dec. 1995)
mk	Tsu, R., et al., "Tunneling in Nanoscale Silicon Particles Embedded in an SiO/sub/2 Matrix", <u>Abstract, IEEE Device Research Conference</u> , 178-179, (1996)

Examiner

Michael Truch

Date Considered

6/30/00

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

91256643

Sheet 8 of 9

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown 280

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
Initial

ms	Tucker, C., et al., "Ion-beam-assisted Deposition of Nonhydrogenated a-Si:C Films", <u>Can. J. Physics</u> , 74, 97-101, (1996)
	van der Weide, J., et al., "Negative-electron-affinity Effects on the Diamond (100) Surface", <u>Physical Review B [Condensed Matter]</u> , 50, 5803-5806, (Aug. 15, 1994)
	Vodakov, Y., et al., "Diffusion and Solubility of Impurities in Silicon Carbide", In: <u>Silicon Carbide</u> , R.C. Marshall, et al., eds., Univ. of South Carolina Press, 508-519, (1973)
	Wahab, Q., et al., "3C-SiC / Si / 3C-SiC Epitaxial Trilayer Films Deposited on Si (111) Substrates by Reactive Magnetron Sputtering", <u>J. Materials Res.</u> , 10, 1349-1351, (June 1995)
	Watanabe, A., et al., "SiC Thin Film Preparation by ArF Excimer Laser Chemical Vapor Deposition. Part 1: Rate of Photolysis of Alkylsilanes by ArF Excimer Laser and their Decomposition Products", <u>Thin Solid Films</u> , 274, 70-75, (1996)
	Wolter, S., et al., "Textured Growth of Diamond on Silicon via in situ Carburization and Bias-Enhanced Nucleation", <u>Appl. Phys. Lett.</u> , 62, 1215-1217, (March 1993)
	Wu, K., et al., "The Growth and Characterization of Silicon/Silicon Carbide Heteroepitaxial Films on Silicon Substrates by Rapid Thermal Chemical Vapor Deposition", <u>Japanese J. Appl. Phys.</u> , 35, 3836-3840, (1996)
	Yamaguchi, Y., et al., "Properties of Heteroepitaxial 3C-SiC Films Grown by LPCVD", <u>Digest of Tech. Papers: 8th Int. Conf. on Solid-State Sensors and Actuators and Eurosensors IX</u> , vol. 2, Stockholm, Sweden, 190-193, (June 1995)
	Yamanashi, H., et al., "Deposition of Silicon Compound Thin Films in DC Discharge Plasma Using Hydrogen-Hexamethyldisilane Gas Mixture", <u>Proc.: Int. Symp. on Surfaces and Thin Films of Electronic Materials. Bull. of the Res. Institute of Electronics, Shizuoka University</u> , 30, 95-98, (1995)
ms	Yee, A., et al., "The Effect of Nitrogen on Pulsed Laser Deposition of Amorphous Silicon Carbide Films: Properties and Structure", <u>J. Materials Research</u> , 11, 1979-1986, (1996)

Examiner	Michael Trill	Date Considered	6/20/00
----------	---------------	-----------------	---------

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

9/256643

Sheet 9 of 9

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown 2822

OTHER DOCUMENTS

**Examiner
Initial

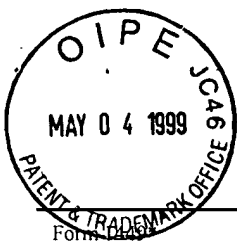
(Including Author, Title, Date, Pertinent Pages, Etc.)

ms | Yoder, M., "Wide Bandgap Semiconductor Materials and Devices", IEEE
Transactions on Electron Devices, 43, 1633-1636, (October 1996)

Examiner	Michael Trill	Date Considered	6/26/00
----------	---------------	-----------------	---------

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

44
Sheet 1 of 1

Form PTO-1449

Atty. Docket No.: 303.324US2

Serial No. 09/256,643

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(Use several sheets if necessary)

Applicants: Leonard Forbes et al.

Filing Date: February 23, 1999

Group: 2822

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
						Yes	No
<u>mt</u>	5,846,859	12/08/1998	Lee, S.	438	253		02/23/96

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
<u>mt</u>	60-184681	09/20/1985	Japan	C23C	16/30	With Abstract	X
<u>mt</u>	60-242678	12/02/1985	Japan	H01L	29/78	With Abstract	X

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
Initial

Examiner

Michael Trim

Date Considered

6/30/00

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



#5

Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. 09/256,643
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: February 23, 1999	Group: 2822

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<u>mt</u>	5,886,368	03/23/1999	Forbes, L., et al.	257	77	07/29/97
<u>mt</u>	5,898,197	04/27/1999	Fujiwara, H.	257	317	06/03/97

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
<u>mt</u>	08-255878-TR	10/01/1996	Japan	H01L	27/10	X

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial	
<u>mt</u>	Sze, S.M., In: <u>Physics of Semiconductor Devices</u> , Wiley-Interscience, New York, p. 496-497, (1969)

RECEIVED
JUL 13 1999
TC 2800 MAIL ROOM

Examiner <u>Michael Trish</u>	Date Considered <u>6/25/00</u>
-------------------------------	--------------------------------

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



#6

Sheet 1 of 1

Form 1449*

Atty. Docket No.: 303.324US2

Serial No. 09/256,643

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT
(Use several sheets if necessary)

Applicant: Leonard Forbes et al.

Filing Date: February 23, 1999

Group: 2822

U.S. PATENT DOCUMENTS

**Examiner		Document Number	Date	Name	Class	Subclass	Filing Date
Initial							If Appropriate
MT		4,849,797	07/18/1989	Ukai, Y., et al.	357	237	01/20/88

FOREIGN PATENT DOCUMENTS

**Examiner		Document Number	Date	Country	Class	Subclass	Translation	
Initial							Yes	No

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner	
Initial	

Examiner

Michael Triest

Date Considered

5/30/00

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



#7

Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. 09/256,643
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: February 23, 1999	Group: 2822

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
						If Appropriate
MT	5,049,950	09/17/1991	Fujii, Y., et al.	357	2	08/09/90

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

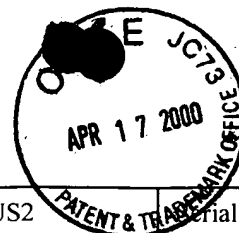
**Examiner Initial	
MT	Sakata, I., et al., "Amorphous silicon/amorphous silicon carbide heterojunctions applied to memory device structures", <u>Electronics Letters</u> , 30(9), pp. 688-689, (April 1994)

RECEIVED
DEC - 1 1993
TELECOMMUNICATIONS ROOM

Examiner <i>Michael Trind</i>	Date Considered <i>6/20/00</i>
----------------------------------	-----------------------------------

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Handwritten initials: HJ

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. 09/256,643
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: February 23, 1999	Group: 2822

U.S. PATENT DOCUMENTS

**Examiner		Document Number	Date	Name	Class	Subclass	Filing Date
Initial							If Appropriate
<i>mt</i>		5,235,195	08/10/1993	Tran, N.T., et al.	257	59	10/19/92
<i>mt</i>		5,415,126	05/16/1995	Loboda, M.J., et al.	117	88	08/16/93
<i>mt</i>		5,455,432	10/03/1995	Hartsell, M.L., et al.	257	77	10/11/94
<i>mt</i>		5,562,769	10/08/1996	Dreifus, D.L., et al.	117	86	02/22/95
<i>mt</i>		5,877,041	03/02/1999	Fuller, R.T.	438	105	06/30/97

FOREIGN PATENT DOCUMENTS

**Examiner		Document Number	Date	Country	Class	Subclass	Translation	
Initial							Yes	No
<i>mt</i>		07-226507	08/22/1995	Japan	H01L	29/78		<input checked="" type="checkbox"/>

OTHER DOCUMENTS

**Examiner Initial	(Including Author, Title, Date, Pertinent Pages, Etc.)
--------------------	--

RECEIVED
APR 20 2000
TECHNOLOGY CENTER 2800

Examiner <i>Michael Triv</i>	Date Considered <i>6/30/00</i>
------------------------------	--------------------------------

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.